Irina A Buyanova

List of Publications by Year
in descending order

349	6,084	109137	110170
papers	citations	35 h-index	64 g-index

353	353	353	5162
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Competition between triplet pair formation and excimer-like recombination controls singlet fission yield. Cell Reports Physical Science, 2021, 2, 100339.	2.8	13
2	An Efficient Deep-Subwavelength Second Harmonic Nanoantenna Based on Surface Plasmon-Coupled Dilute Nitride GaNP Nanowires. Nano Letters, 2021, 21, 3426-3434.	4.5	6
3	Room-temperature electron spin polarization exceeding 90% in an opto-spintronic semiconductor nanostructure via remote spin filtering. Nature Photonics, 2021, 15, 475-482.	15.6	27
4	Exciton generation and recombination dynamics of quantum dots embedded in GaNAsP nanowires. Physical Review B, 2021, 103, .	1.1	1
5	Anomalously Strong Secondâ€Harmonic Generation in GaAs Nanowires via Crystalâ€Structure Engineering. Advanced Functional Materials, 2021, 31, 2104671.	7.8	9
6	Magneto-optical properties of Cr3+ in Î²-Ga2O3. Applied Physics Letters, 2021, 119, .	1.5	15
7	Identifying a Generic and Detrimental Role of Fano Resonance in Spin Generation in Semiconductor Nanostructures. Physical Review Letters, 2021, 127, 127401.	2.9	2
8	Molecular beam epitaxial growth of GaAs/GaNAsBi coreâ€“multishell nanowires. Applied Physics Express, 2021, 14, 115002.	1.1	3
9	Effects of growth temperature and thermal annealing on optical quality of GaNAs nanowires emitting in the near-infrared spectral range. Nanotechnology, 2020, 31, 065702.	1.3	5
10	Oblique Nuclear Quadrupole Interaction in Self-Assembled Structures Based on Semiconductor Quantum Dots. Physical Review Applied, 2020, 14, .	1.5	1
11	Self-assembled nanodisks in coaxial GaAs/GaAsBi/GaAs coreâ€“multishell nanowires. Nanoscale, 2020, 12, 20849-20858.	2.8	6
12	Nearâ€Infrared Lightâ€Responsive Cuâ€Doped Cs₂AgBiBr₆. Advanced Functional Materials, 2020, 30, 2005521.	7.8	56
13	Magnetizing lead-free halide double perovskites. Science Advances, 2020, 6, .	4.7	56
14	Effect of Crystal Symmetry on the Spin States of Fe³⁺ and Vibration Modes in Lead-free Double-Perovskite Cs₂AgBi(Fe)Br₆. Journal of Physical Chemistry Letters, 2020, 11, 4873-4878.	2.1	11
15	Effects of thermal annealing on localization and strain in core/multishell GaAs/GaNAs/GaAs nanowires. Scientific Reports, 2020, 10, 8216.	1.6	6
16	Outermost AlGaO x native oxide as a protection layer for GaAs/AlGaAs core-multishell nanowires. Applied Physics Express, 2020, 13, 075003.	1.1	3
17	Thermal-annealing effects on energy level alignment at organic heterojunctions and corresponding voltage losses in all-polymer solar cells. Nano Energy, 2020, 72, 104677.	8.2	16
18	Scattering symmetry-breaking induced spin photocurrent from out-of-plane spin texture in a 3D topological insulator. Scientific Reports, 2020, 10, 10610.	1.6	2

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19	Effects of Bi incorporation on recombination processes in wurtzite GaBiAs nanowires. Nanotechnology, 2020, 31, 225706.	1.3	5
20	Vibronic coherence contributes to photocurrent generation in organic semiconductor heterojunction diodes. Nature Communications, 2020, 11, 617.	5.8	28
21	Formation, electronic structure, and optical properties of self-assembled quantum-dot single-photon emitters in Ga(N,As,P) nanowires. Physical Review Materials, 2020, 4, .	0.9	4
22	Gallium vacanciesâ€"common non-radiative defects in ternary GaAsP and quaternary GaNAsP nanowires. Nano Express, 2020, 1, 020022.	1.2	2
23	Effect of exciton transfer on recombination dynamics in vertically nonuniform GaAsSb epilayers. Applied Physics Letters, 2019, 114, .	1.5	7
24	Effects of N implantation on defect formation in ZnO nanowires. Thin Solid Films, 2019, 687, 137449.	0.8	9
25	Increasing N content in GaNAsP nanowires suppresses the impact of polytypism on luminescence. Nanotechnology, 2019, 30, 405703.	1.3	6
26	Band Structure of Wurtzite GaBiAs Nanowires. Nano Letters, 2019, 19, 6454-6460.	4.5	7
27	Identification of a Nitrogen-related acceptor in ZnO nanowires. Nanoscale, 2019, 11, 10921-10926.	2.8	5
28	Measurements of Strain and Bandgap of Coherently Epitaxially Grown Wurtzite InAsPâ€"InP Coreâ€"Shell Nanowires. Nano Letters, 2019, 19, 2674-2681.	4.5	16
29	Dilute nitrides-based nanowiresâ€"a promising platform for nanoscale photonics and energy technology. Nanotechnology, 2019, 30, 292002.	1.3	13
30	Molecular beam epitaxial growth of dilute nitride GaNAs and GaInNAs nanowires. Nanotechnology, 2019, 30, 244002.	1.3	9
31	Effects of surface finish on the initial oxidation of HVAF-sprayed NiCoCrAlY coatings. Surface and Coatings Technology, 2019, 364, 43-56.	2.2	25
32	Electron paramagnetic resonance signatures of Co2+ and Cu2+ in Î² -Ga2O3. Applied Physics Letters, 2019, 115, .	1.5	11
33	Near-Infrared Lasing at 1 Î¼m from a Dilute-Nitride-Based Multishell Nanowire. Nano Letters, 2019, 19, 885-890.	4.5	28
34	Photoelectrochemical response of GaN, InGaN, and GaNP nanowire ensembles. Journal of Applied Physics, 2018, 123, 175703.	1.1	4
35	Effect of a Phonon Bottleneck on Exciton and Spin Generation in Self-Assembled <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>In</mml:mi></mml:mrow><mml:mrow><mml:mn>1</mml:mn><mml:mn> Quantum Dots. Physical Review Applied, 2018, 9, .	1.5	8
36	N -induced Quantum Dots in GaAs/Ga(N,As) Core/Shell Nanowires: Symmetry, Strain, and Electronic Structure. Physical Review Applied, 2018, 10, .	1.5	6

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37	Room-temperature polarized spin-photon interface based on a semiconductor nanodisk-in-nanopillar structure driven by few defects. Nature Communications, 2018, 9, 3575.	5.8	16
38	Charge Generation via Relaxed Charge-Transfer States in Organic Photovoltaics by an Energy-Disorder-Driven Entropy Gain. Journal of Physical Chemistry C, 2018, 122, 12640-12646.	1.5	24
39	Photon upconversion promoted by defects in low-dimensional semiconductor nanostructures. , 2018, , 189-210.		1
40	Defects in one-dimensional nanowires. , 2018, , 63-85.		1
41	Defect-enabled room-temperature spin functionalities in a nonmagnetic semiconductor. , 2018, , 265-284.		0
42	Effects of Strong Band-Tail States on Exciton Recombination Dynamics in Dilute Nitride GaP/GaNP Core/Shell Nanowires. Journal of Physical Chemistry C, 2018, 122, 19212-19218.	1.5	10
43	Design rules for minimizing voltage losses in high-efficiency organic solar cells. Nature Materials, 2018, 17, 703-709.	13.3	701
44	GaAs/GaNAs core-multishell nanowires with nitrogen composition exceeding 2%. Applied Physics Letters, 2018, 113, .	1.5	16
45	Efficient Auger Charge-Transfer Processes in ZnO. Physical Review Applied, 2018, 9, .	1.5	1
46	Effects of Nitrogen Incorporation on Structural and Optical Properties of GaNAsP Nanowires. Journal of Physical Chemistry C, 2017, 121, 7047-7055.	1.5	12
47	Luminescent and Optically Detected Magnetic Resonance Studies of CdS/PVA Nanocomposite. Nanoscale Research Letters, 2017, 12, 130.	3.1	9
48	Dilute Nitride Nanowire Lasers Based on a GaAs/GaNAs Core/Shell Structure. Nano Letters, 2017, 17, 1775-1781.	4.5	45
49	Room-temperature InP/InAsP Quantum Discs-in-Nanowire Infrared Photodetectors. Nano Letters, 2017, 17, 3356-3362.	4.5	36
50	Spin injection and helicity control of surface spin photocurrent in a three dimensional topological insulator. Nature Communications, 2017, 8, 15401.	5.8	36
51	Room Temperature Defect-Engineered Spin Functionalities: Concept and Optimization. , 2017, , 33-54.		0
52	Study of the carrier transfer across the GaNP nanowire electrolyte interface by electron paramagnetic spin trapping. Applied Physics Letters, 2017, 110, 222101.	1.5	2
53	Self-catalyzed core-shell GaAs/GaNAs nanowires grown on patterned Si (111) by gas-source molecular beam epitaxy. Applied Physics Letters, 2017, 111, .	1.5	7
54	GaNAs-Based Nanowires for Near-Infrared Optoelectronics. , 2017, , 133-159.		0

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55	Novel GaNP Nanowires for Advanced Optoelectronics and Photonics. , 2017, , 107-132.		0
56	Coreâ€“shell carrier and exciton transfer in GaAs/GaNAs coaxial nanowires. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, 04J104.	0.6	5
57	Thermal stability of the prominent compensating (AlZnâ€“VZn) center in ZnO. Journal of Applied Physics, 2016, 119, 105702.	1.1	6
58	Novel GaNAs and GaNP-based nanowires â€” Promising materials for optoelectronics and photonics. , 2016, , .		1
59	Characterization of quantum dot-like emission from GaAs/GaNAs core/shell nanowires. , 2016, , .		0
60	Defect formation in GaAs/GaNxAs1-x core/shell nanowires. Applied Physics Letters, 2016, 109, .	1.5	12
61	Phosphorescence of CdS nanoparticles in polymer matrix as an indication of host-guest interaction. Materials Chemistry and Physics, 2016, 177, 379-383.	2.0	2
62	Strongly polarized quantum-dot-like light emitters embedded in GaAs/GaNAs core/shell nanowires. Nanoscale, 2016, 8, 15939-15947.	2.8	22
63	Novel GaP/GaNP core/shell nanowires for optoelectronics and photonics. , 2016, , .		1
64	Spin injection and detection in semiconductor nanostructures. , 2016, , .		0
65	Spin injection loss in self-assembled InAs/GaAs quantum dot structures from disordered barrier layers. , 2016, , .		0
66	Unintentional nitrogen incorporation in ZnO nanowires detected by electron paramagnetic resonance spectroscopy. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 572-575.	0.8	1
67	Understanding and optimizing spin injection in self-assembled InAs/GaAs quantum-dot molecular structures. Nano Research, 2016, 9, 602-611.	5.8	8
68	Structural properties of GaNAs nanowires probed by micro-Raman spectroscopy. Semiconductor Science and Technology, 2016, 31, 025002.	1.0	4
69	Spin-Polarized Light Emitting Self-Assembled InAs/GaAs Quantum-Dot Molecular Structures: The Dominant Mechanism for Spin Loss during Spin Injection. ECS Meeting Abstracts, 2016, , .	0.0	0
70	Effects of N Incorporation on Carrier Recombination in GaAs-Based Nanowires Grown By Molecular Beam Epitaxy on Si Substrates. ECS Meeting Abstracts, 2016, , .	0.0	0
71	Suppression of non-radiative surface recombination by N incorporation in GaAs/GaNAs core/shell nanowires. Scientific Reports, 2015, 5, 11653.	1.6	35
72	Efficient nitrogen incorporation in ZnO nanowires. Scientific Reports, 2015, 5, 13406.	1.6	21

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73	Fabryâ€“Perot Microcavity Modes in Single GaP/GaNP Core/Shell Nanowires. Small, 2015, 11, 6331-6337.	5.2	13
74	Growth of isotopically enriched ZnO nanorods of excellent optical quality. Journal of Crystal Growth, 2015, 429, 6-12.	0.7	11
75	Effects of Polytypism on Optical Properties and Band Structure of Individual Ga(N)P Nanowires from Correlative Spatially Resolved Structural and Optical Studies. Nano Letters, 2015, 15, 4052-4058.	4.5	19
76	Interfacial bonding in a CdS/PVA nanocomposite: A Raman scattering study. Journal of Colloid and Interface Science, 2015, 452, 33-37.	5.0	20
77	Enhancement of polymer endurance to UV light by incorporation of semiconductor nanoparticles. Nanoscale Research Letters, 2015, 10, 81.	3.1	29
78	Exciton Fine-Structure Splitting in Self-Assembled Lateral InAs/GaAs Quantum-Dot Molecular Structures. ACS Nano, 2015, 9, 5741-5749.	7.3	7
79	Dual-wavelength excited photoluminescence spectroscopy of deep-level hole traps in Ga(In)NP. Journal of Applied Physics, 2015, 117, 015701.	1.1	2
80	Size dependence of electron spin dephasing in InGaAs quantum dots. Applied Physics Letters, 2015, 106, 093109.	1.5	6
81	Optimizing GaNP Coaxial Nanowires for Efficient Light Emission by Controlling Formation of Surface and Interfacial Defects. Nano Letters, 2015, 15, 242-247.	4.5	20
82	Energy Upconversion in GaP/GaNP Core/Shell Nanowires for Enhanced Nearâ€Infrared Light Harvesting. Small, 2014, 10, 4403-4408.	5.2	26
83	Magneto-optical properties and recombination dynamics of isoelectronic bound excitons in ZnO. , 2014, , .		1
84	Defect properties of ZnO nanowires. , 2014, , .		5
85	Origin of radiative recombination and manifestations of localization effects in GaAs/GaNAs core/shell nanowires. Applied Physics Letters, 2014, 105, .	1.5	27
86	Raman spectroscopy of GaP/GaNP core/shell nanowires. Applied Physics Letters, 2014, 105, 193102.	1.5	20
87	Limiting factor of defect-engineered spin-filtering effect at room temperature. Physical Review B, 2014, 89, .	1.1	5
88	Anomalous spectral dependence of optical polarization and its impact on spin detection in InGaAs/GaAs quantum dots. Applied Physics Letters, 2014, 105, 132106.	1.5	11
89	Recharging behavior of nitrogen-centers in ZnO. Journal of Applied Physics, 2014, 116, .	1.1	10
90	Spin dynamics of isoelectronic bound excitons in ZnO. Physical Review B, 2014, 89, .	1.1	1

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91	Turning ZnO into an Efficient Energy Upconversion Material by Defect Engineering. Advanced Functional Materials, 2014, 24, 3760-3764.	7.8	36
92	Identification of an isolated arsenic antisite defect in GaAsBi. Applied Physics Letters, 2014, 104, 052110.	1.5	17
93	Origin of Strong Photoluminescence Polarization in GaNP Nanowires. Nano Letters, 2014, 14, 5264-5269.	4.5	22
94	Growth and characterization of dilute nitride GaNxP1â^'x nanowires and GaNxP1â^'x/GaNyP1â^'y core/shell nanowires on Si (111) by gas source molecular beam epitaxy. Applied Physics Letters, 2014, 105, .	1.5	36
95	Zinc-Vacancyâ€"Donor Complex: A Crucial Compensating Acceptor in ZnO. Physical Review Applied, 2014, 2, .	1.5	51
96	Effects of Ni-coating on ZnO nanowires: A Raman scattering study. Journal of Applied Physics, 2013, 113, 214302.	1.1	18
97	Cathodoluminescence characterization of ZnO tetrapod structures. Thin Solid Films, 2013, 543, 114-117.	0.8	6
98	Effect of thermal annealing on defects in post-growth hydrogenated GaNP. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 561-563.	0.8	3
99	Optical properties of GaP/GaNP core/shell nanowires: a temperature-dependent study. Nanoscale Research Letters, 2013, 8, 239.	3.1	7
100	Roomâ€Temperature Electron Spin Amplifier Based on Ga(In)NAs Alloys. Advanced Materials, 2013, 25, 738-742.	11.1	23
101	Defect properties of ZnO nanowires revealed from an optically detected magnetic resonance study. Nanotechnology, 2013, 24, 015701.	1.3	15
102	Efficient room-temperature nuclear spin hyperpolarization of a defect atom in a semiconductor. Nature Communications, 2013, 4, 1751.	5.8	33
103	Dynamics of donor bound excitons in ZnO. Applied Physics Letters, 2013, 102, .	1.5	16
104	Role of the host polymer matrix in light emission processes in nano-CdS/poly vinyl alcohol composite. Thin Solid Films, 2013, 543, 11-15.	0.8	11
105	Defects in N, O and N, Zn implanted ZnO bulk crystals. Journal of Applied Physics, 2013, 113, .	1.1	34
106	Optically detected magnetic resonance studies of point defects in quaternary GaNAsP epilayers grown by vapor phase epitaxy. Applied Physics Letters, 2013, 102, 021910.	1.5	9
107	Effect of hyperfine-induced spin mixing on the defect-enabled spin blockade and spin filtering in GaNAs. Physical Review B, 2013, 87, .	1.1	12
108	Effects of a longitudinal magnetic field on spin injection and detection in InAs/GaAs quantum dot structures. Journal of Physics Condensed Matter, 2012, 24, 145304.	0.7	4

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109	Evidence for coupling between exciton emissions and surface plasmon in Ni-coated ZnO nanowires. Nanotechnology, 2012, 23, 425201.	1.3	35
110	Sub-millisecond dynamic nuclear spin hyperpolarization in a semiconductor: A case study from PInantisite in InP. Physical Review B, 2012, 86, .	1.1	2
111	Zeeman splitting and dynamics of an isoelectronic bound exciton near the band edge of ZnO. Physical Review B, 2012, 86, .	1.1	5
112	Temperature dependence of dynamic nuclear polarization and its effect on electron spin relaxation and dephasing in InAs/GaAs quantum dots. Applied Physics Letters, 2012, 100, .	1.5	4
113	Efficient upconversion of photoluminescence via two-photon absorption in bulk and nanorod ZnO. Applied Physics B: Lasers and Optics, 2012, 108, 919-924.	1.1	26
114	Effects of Ultraviolet Light on Optical Properties of Colloidal CdS Nanoparticles Embedded in Polyvinyl Alcohol (PVA) Matrix. Advanced Science, Engineering and Medicine, 2012, 4, 394-400.	0.3	11
115	Effects of hydrogenation on non-radiative defects in GaNP and GaNAs alloys: An optically detected magnetic resonance study. Journal of Applied Physics, 2012, 111, 023501.	1.1	4
116	Mechanism for radiative recombination and defect properties of GaP/GaNP core/shell nanowires. Applied Physics Letters, 2012, 101, 163106.	1.5	30
117	Antiferromagnetic interaction in coupled CdSe/ZnMnSe quantum dot structures. Applied Physics Letters, 2012, 101, 052405.	1.5	4
118	The Hanle effect and electron spin polarization in InAs/GaAs quantum dots up to room temperature. Nanotechnology, 2012, 23, 135705.	1.3	4
119	Effects of P implantation and post-implantation annealing on defect formation in ZnO. Journal of Applied Physics, 2012, 111, 043520.	1.1	6
120	Long delays of light in ZnO caused by excitonâ€polariton propagation. Physica Status Solidi (B): Basic Research, 2012, 249, 1307-1311.	0.7	0
121	Back Cover: Long delays of light in ZnO caused by exciton-polariton propagation (Phys. Status Solidi B) Tj ETQq1 1 0.784314 rgBT /Ov	0.7	0
122	Catalytic conversion of C2-C3 alcohols on detonation nanodiamond and its modifications. Russian Journal of Physical Chemistry A, 2012, 86, 26-31.	0.1	18
123	Efficient room-temperature spin detector based on GaNAs. Journal of Applied Physics, 2012, 111, 07C303.	1.1	9
124	Donor bound excitons involving a hole from the B valence band in ZnO: Time resolved and magneto-photoluminescence studies. Applied Physics Letters, 2011, 99, 091909.	1.5	9
125	Room-temperature spin injection and spin loss across a GaNAs/GaAs interface. Applied Physics Letters, 2011, 98, 012112.	1.5	7
126	Slowdown of light due to exciton-polariton propagation in ZnO. Physical Review B, 2011, 83, .	1.1	13

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127	Room temperature spin filtering effect in GaNAs: Role of hydrogen. Applied Physics Letters, 2011, 99, 152109.	1.5	7
128	Effect of postgrowth hydrogen treatment on defects in GaNP. Applied Physics Letters, 2011, 98, 141920.	1.5	9
129	Strong room-temperature optical and spin polarization in InAs/GaAs quantum dot structures. Applied Physics Letters, 2011, 98, .	1.5	19
130	Efficiency of spin injection in novel InAs quantum dot structures: exciton vs. free carrier injection. Journal of Physics: Conference Series, 2010, 245, 012044.	0.3	4
131	Spin Dynamics in ZnO-Based Materials. Journal of Superconductivity and Novel Magnetism, 2010, 23, 161-165.	0.8	7
132	Paramagnetic centers in detonation nanodiamonds studied by CW and pulse EPR. Chemical Physics Letters, 2010, 493, 319-322.	1.2	21
133	On the origin of suppression of free exciton no-phonon emission in ZnO tetrapods. Applied Physics Letters, 2010, 96, .	1.5	12
134	Evidence for a phosphorus-related interfacial defect complex at a GaP/GaNP heterojunction. Physical Review B, 2010, 81, .	1.1	11
135	Long lifetime of free excitons in ZnO tetrapod structures. Applied Physics Letters, 2010, 96, .	1.5	30
136	Electron spin filtering by thin GaNAs/GaAs multiquantum wells. Applied Physics Letters, 2010, 96, .	1.5	31
137	Dominant recombination centers in Ga(In)NAs alloys: Ga interstitials. Applied Physics Letters, 2009, 95, .	1.5	57
138	Spin injection in lateral InAs quantum dot structures by optical orientation spectroscopy. Nanotechnology, 2009, 20, 375401.	1.3	12
139	Electron spin control in dilute nitride semiconductors. Journal of Physics Condensed Matter, 2009, 21, 174211.	0.7	14
140	Propagation dynamics of exciton spins in a highâ€density semiconductor quantum dot system. Physica Status Solidi C: Current Topics in Solid State Physics, 2009, 6, 50-52.	0.8	0
141	Room-temperature defect-engineered spin filter based on a non-magnetic semiconductor. Nature Materials, 2009, 8, 198-202.	13.3	94
142	Effects of Ga doping on optical and structural properties of ZnO epilayers. Superlattices and Microstructures, 2009, 45, 413-420.	1.4	9
143	Transfer dynamics of spin-polarized excitons into semiconductor quantum dots. Journal of Luminescence, 2009, 129, 1927-1930.	1.5	1
144	Oxygen and zinc vacancies in as-grown ZnO single crystals. Journal Physics D: Applied Physics, 2009, 42, 175411.	1.3	117

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145	Efficient Spin Filter Based on Non-Magnetic Semiconductor GaNAs. , 2009, , .		0
146	Magneto-optical and tunable laser excitation spectroscopy of spin-injection and spin loss from Zn(Cd)MnSe diluted magnetic quantum well to CdSe non-magnetic quantum dots. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2008, 147, 262-266.	1.7	1
147	Spin injection in a coupled system of a diluted magnetic semiconductor Zn0.80Mn0.20Se and self-assembled quantum dots of CdSe. Superlattices and Microstructures, 2008, 43, 615-619.	1.4	0
148	Effect of growth conditions on grownâ€in defect formation and luminescence efficiency in Ga(In)NP epilayers grown by molecularâ€beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 460-463.	0.8	0
149	Effects of grown-in defects on electron spin polarization in dilute nitride alloys. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1529-1531.	0.8	0
150	Optical and electronic properties of GaInNP alloys â€“ a new material system for lattice matching to GaAs. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 101-106.	0.8	1
151	Spin resonance spectroscopy of grown-in defects in Ga(In)NP alloys. Superlattices and Microstructures, 2008, 43, 620-625.	1.4	0
152	Effects of hydrogen on the optical properties of ZnCdOâˆ•ZnO quantum wells grown by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 261912.	1.5	22
153	Formation of grown-in defects in molecular beam epitaxial Ga(In)NP: Effects of growth conditions and postgrowth treatments. Journal of Applied Physics, 2008, 103, 063519.	1.1	14
154	Migration and luminescence enhancement effects of deuterium in ZnOâˆ•ZnCdO quantum wells. Applied Physics Letters, 2008, 92, .	1.5	11
155	Dominant factors limiting efficiency of optical spin detection in ZnO-based materials. Applied Physics Letters, 2008, 92, 092103.	1.5	18
156	Spin-Conserving Tunneling of Excitons in Diluted Magnetic Semiconductor Double Quantum Wells. Japanese Journal of Applied Physics, 2008, 47, 3533-3536.	0.8	4
157	Effects of stoichiometry on defect formation in ZnO epilayers grown by molecular-beam epitaxy: An optically detected magnetic resonance study. Journal of Applied Physics, 2008, 103, 023712.	1.1	18
158	Efficiency of optical spin injection and spin loss from a diluted magnetic semiconductor ZnMnSe to CdSe nonmagnetic quantum dots. Physical Review B, 2008, 77, .	1.1	16
159	Transfer Dynamics of Spin-Polarized Excitons in ZnCdMnSe/ZnCdSe Double Quantum Wells. Journal of the Korean Physical Society, 2008, 53, 167-170.	0.3	0
160	Spin-Injection Dynamics and Effects of Spin Relaxation in Self-Assembled Quantum Dots of CdSe. Journal of the Korean Physical Society, 2008, 53, 163-166.	0.3	0
161	Optical and Electronic Properties of GaInNP Alloys: A New Material for Lattice Matching to GaAs. , 2008, , 301-316.		0
162	Dynamics of exciton-spin injection, transfer, and relaxation in self-assembled quantum dots of CdSe coupled with a diluted magnetic semiconductor layer ofZn0.80Mn0.20Se. Physical Review B, 2007, 75, .	1.1	22

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163	Transition Metal Doped ZnO for Spintronics. Materials Research Society Symposia Proceedings, 2007, 999, 1.	0.1	6
164	Prospects of Potential Semiconductor Spin Detectors. Solid State Phenomena, 2007, 124-126, 839-842.	0.3	0
165	Magneto-optical spectroscopy of spin injection and spin relaxation in ZnMnSe/ZnCdSe and GaMnN/InGaN spin light-emitting structures. Physica Status Solidi (A) Applications and Materials Science, 2007, 204, 159-173.	0.8	2
166	Hydrogen passivation of nitrogen in GaNAs and GaNP alloys: How many H atoms are required for each N atom?. Applied Physics Letters, 2007, 90, 021920.	1.5	9
167	Optically detected cyclotron resonance studies of InxGa1âˆ’xNyAs1âˆ’yâ•GaAs quantum wells sandwiched between type-II AlAsâ•GaAs superlattices. Journal of Applied Physics, 2007, 101, 073705.	1.1	3
168	Spin Dynamics of Type-II Excitons in Diluted Magnetic Double Quantum Wells. AIP Conference Proceedings, 2007, , .	0.3	0
169	Role of Nitrogen In Photoluminescence Up-conversion In GaInNP/GaAs Heterostructures. AIP Conference Proceedings, 2007, , .	0.3	0
170	Optically detected cyclotron resonance studies of InGaNAs/GaAs structures. AIP Conference Proceedings, 2007, , .	0.3	0
171	Optical characterization studies of grown-in defects in ZnO epilayers grown by molecular beam epitaxy. Physica B: Condensed Matter, 2007, 401-402, 413-416.	1.3	4
172	ZnO Doped With Transition Metal Ions. IEEE Transactions on Electron Devices, 2007, 54, 1040-1048.	1.6	137
173	Mechanism for radiative recombination in ZnCdO alloys. Applied Physics Letters, 2007, 90, 261907.	1.5	23
174	Ferromagnetism in Transition-Metal Doped ZnO. Journal of Electronic Materials, 2007, 36, 462-471.	1.0	90
175	Metamorphic InGaAs quantum wells for light emission at 1.3â€“1.6ÂÎ¼m. Thin Solid Films, 2007, 515, 4348-4351.	0.8	6
176	Radiative recombination of GaInNP alloys lattice matched to GaAs. Applied Physics Letters, 2006, 88, 011919.	1.5	8
177	Modeling of band gap properties of GaInNP alloys lattice matched to GaAs. Applied Physics Letters, 2006, 88, 031907.	1.5	15
178	Ferromagnetism in ZnO Doped with Transition Metal Ions. , 2006, , 555-576.		1
179	Band gap properties of Zn1âˆ’xCdxO alloys grown by molecular-beam epitaxy. Applied Physics Letters, 2006, 89, 151909.	1.5	71
180	Spin depolarization in semiconductor spin detectors. , 2006, , .		0

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181	Unusual effects of hydrogen on electronic and lattice properties of GaNP alloys. Physica B: Condensed Matter, 2006, 376-377, 568-570.	1.3	1
182	Signatures of grown-in defects in GaInNP alloys grown on a GaAs substrate from magnetic resonance studies. Physica B: Condensed Matter, 2006, 376-377, 571-574.	1.3	0
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